

## SOT-23 Plastic-Encapsulate MOSFETs

### 2N7002K N-channel MOSFET

#### FEATURES

- High density cell design for Low  $R_{DS(on)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability
- ESD protected up to 2KV

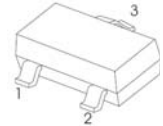
Marking: 72K

#### MOSFET MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ unless otherwise noted)

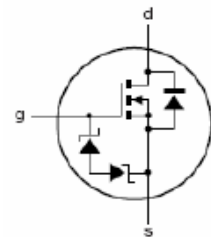
Symbol	Parameter	Value	Units
$V_{DS}$	Drain-Source voltage	60	V
$I_D$	Drain Current	340	mA
$P_D$	Power Dissipation	0.35	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	357	$^\circ\text{C/W}$

#### SOT-23

1. GATE
2. SOURCE
3. DRAIN



#### Equivalent circuit



#### MOSFET ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Gate Threshold Voltage*	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1mA$	1			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 48V, V_{GS} = 0V$			1	$\mu A$
Gate -Source leakage current	$I_{GSS1}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 10$	$\mu A$
	$I_{GSS2}$	$V_{GS} = \pm 10V, V_{DS} = 0V$			$\pm 200$	nA
	$I_{GSS3}$	$V_{GS} = \pm 5V, V_{DS} = 0V$			$\pm 100$	nA
Drain-Source On-Resistance*	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 200mA$			5.3	$\Omega$
		$V_{GS} = 10V, I_D = 500mA$			5	$\Omega$
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 300mA$			1.5	V
Recovered charge	$Q_r$	$V_{GS} = 0V, I_S = 300mA, V_R = 25V, di/dt = -100A/\mu S$		30		nC
<b>Dynamic Characteristics**</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$			40	pF
Output Capacitance	$C_{oss}$				30	pF
Reverse Transfer Capacitance	$C_{rss}$				10	pF
<b>Switching Characteristics**</b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DD} = 50V, R_G = 50\Omega, R_{GS} = 50\Omega, R_L = 250\Omega$			10	ns
Turn-Off Delay Time	$t_{d(off)}$				15	ns
Reverse recovery Time	$t_{rr}$	$V_{GS} = 0V, I_S = 300mA, V_R = 25V, di/dt = -100A/\mu S$		30		ns
<b>GATE-SOURCE ZENER DIODE</b>						
Gate-Source Breakdown Voltage	$BV_{GSO}$	$I_{GS} = \pm 1mA$ (Open Drain)	$\pm 21.5$		$\pm 30$	V

#### Notes :

\*Pulse Test : Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .

\*\*These parameters have no way to verify.

# Typical Characteristics

# 2N7002K

